

PHOTOSENSOR MODULE

TYPE : H10770B-40

CUSTOMER: UNIV OF CALIF SAN DIEGO

QUANTITY: 4 pcs.

Serial Number	(1) Cathode Radiant Sens. mA/W	(2) Anode Radiant Sens. A/W $\times 10^3$	(3) Anode Dark Current nA				
	AA4495	204.0	253	0.14			
AA4803	228.0	258	0.57				
AA4948	233.0	613	0.51				
AA5097	246.0	2130	1.79				

NOTES

- (1) (2) The light source is a tungsten lamp and the incident light on the photocathode has a wavelength of 550 nm which is obtained through band pass filter.
- (2) (3) Overall control voltage: 0.8 V
- (3) Temp setting 25 °C

Date: MARCH 15, 2012

Approved by :



PRELIMINARY

H10770B-40/-50 Specifications

W/O PROTECTION CIRCUIT

□ Maximum Ratings

Parameter	-40/-50	Unit
Main unit input voltage	+18	V dc
Operating temperature	+5 to +35	Cel
Storage temperature	-20 to +50	Cel
Output Current	2	μA
Control Voltage (Vcontrol)	+0.9(Input impedance for Vcont. is 100 kΩ)	V

□ Specifications General

(Ta = 25 Cel)

Parameter	-40	-50	Unit
Spectral response	300 to 720	380 to 890	nm
High voltage power supply and Voltage Regulator Supply voltage range	+11.5 to +15.5		V dc
High voltage power supply and Voltage Regulator Supply Current Requirement (Maximum)	62		mA
Supply Adjustable Range (Relative Sensitivity)	1:50		-
Setting Time(Sensitivity Control) ^{*1}	0.2		s
Effective Area (dia.)	5		mm
Weight (Approx.)	110		g

*1) Stabilized time in the control voltage adjustment from +1.0 V to +0.5 V.

□ Series Characteristics

(Ta = 25 Cel)

Parameter		-40	-50	Unit
H10770	Radiant Sensitivity	at 420 nm	54	Typical × 10 ⁻⁶ A/nW
		at 550 nm	88	
		at 800 nm	-	
Dark Current ^{(A)(B)}	Typical	3.3	4.1	nA
	Maximum	9.3	11.6	
H10770P	Radiant Sensitivity	at 420 nm	108	Typical × 10 ⁻⁶ A/nW
		at 550 nm	176	
		at 800 nm	-	
Dark Count ^{(B)(C)}	Typical	6000	7500	1/s
	Maximum	18000	22500	
Induced Ripple in Signal ^(D)		0.6		Maximum mV p-p
Anode Pulse Rise Time ^(A)		1.00		ns
Recommended Control Voltage Range Vcontrol		+0.50 to +0.80		V

(A) Control Voltage : +0.8 V ; Temperature control at 25 Cel.

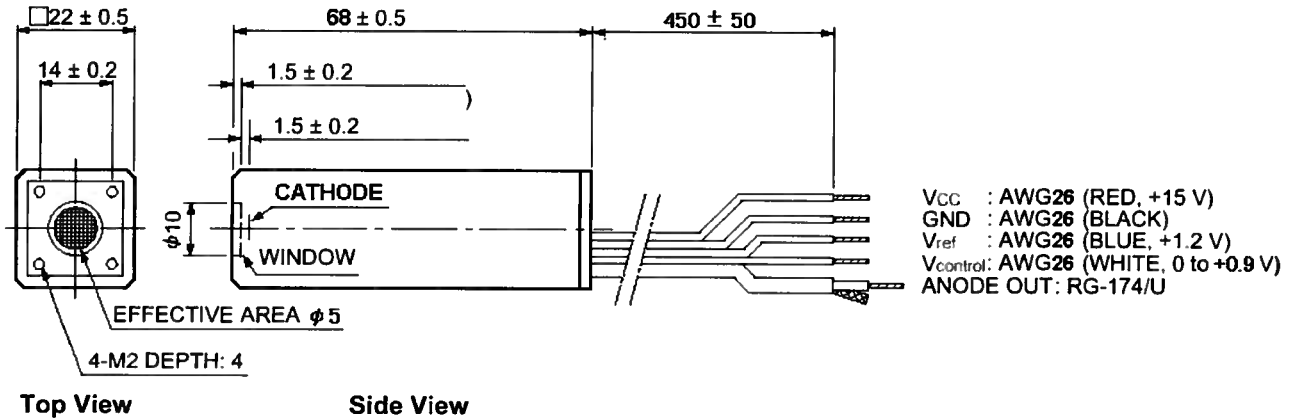
(B) After 30 min storage in darkness.

(C) Control Voltage : Plateau ; Temperature control at 25 Cel.

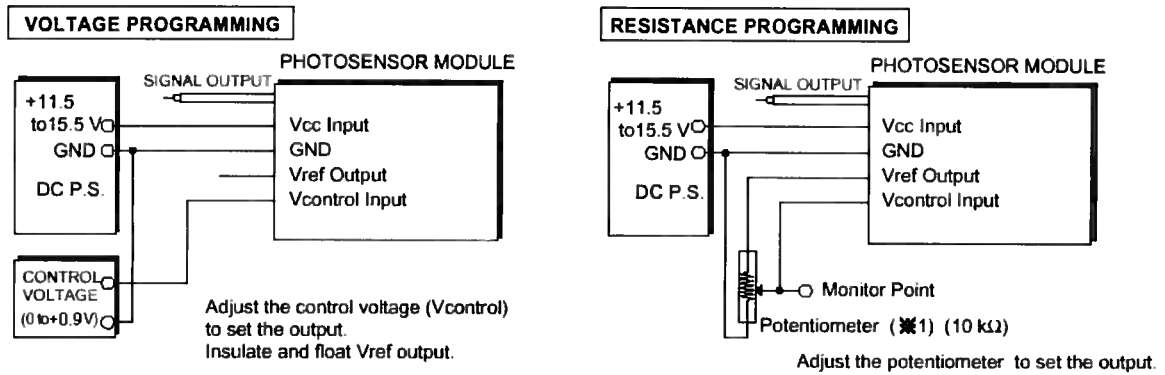
(D) Measured across 1 MOhm / 22 pF load

□ Dimensions

Unit : mm

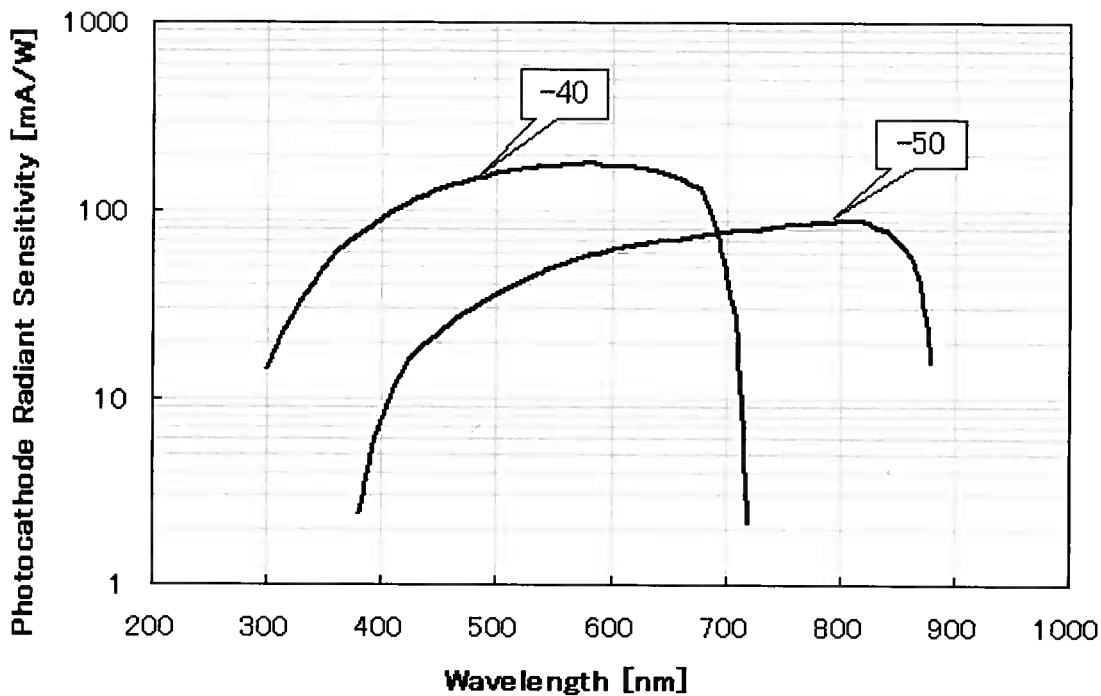


□ Wiring Examples For Sensitivity Adjustment

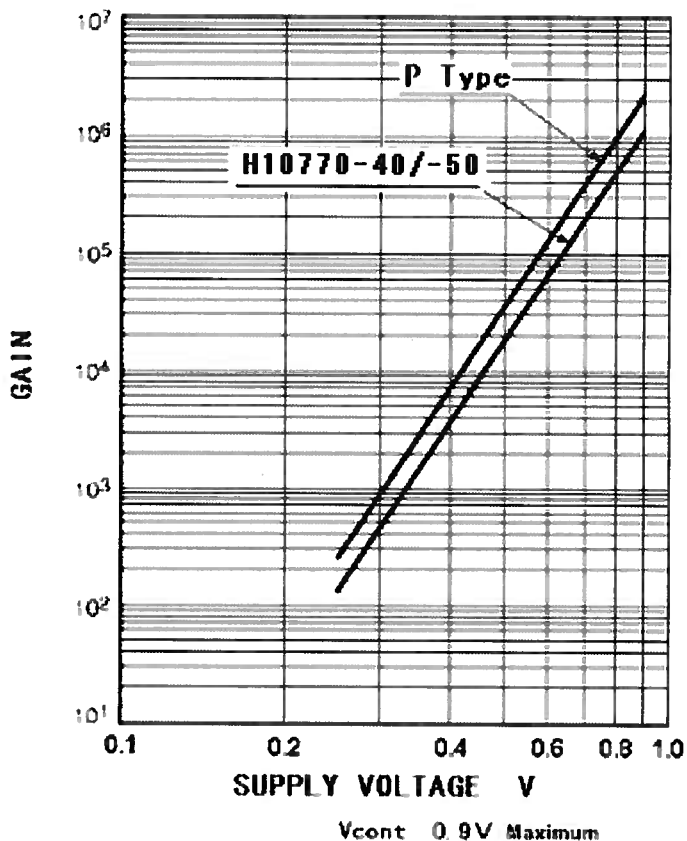


※1 It is recommended to monitor the control voltage with a multimeter and adjust the voltage within maximum +0.9 V.

□ Typical Spectral Photocathode Radiant Sensitivity
(H10770(P)-40/-50)

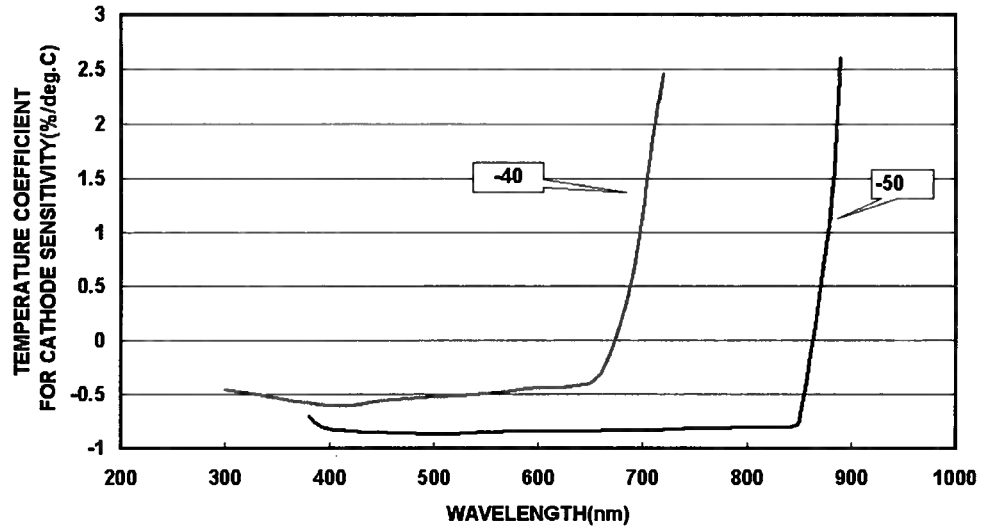


□ Typical Gain Characteristics
(H10770(P)-40/-50)



Temperature control at 10 Cel

□ Temperature Coefficient



For further information, contact our sales office in your country.

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Characteristics and specifications are subject to change without prior notice.

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PHOTOSENSOR MODULE

TYPE : H10770A-40

CUSTOMER: UNIV OF CALIF SAN DIEGO

QUANTITY: 2 pcs.

Serial Number	(1) Cathode Radiant Sens. mA/W	(2) Anode Radiant Sens. A/W	(3) Anode Dark Current nA	Serial Number	(1) Cathode Radiant Sens. mA/W	(2) Anode Radiant Sens. A/W	(3) Anode Dark Current nA
	AA1749 AA1885	187.7 198.4	321000 260000		0.7 0.7		

NOTES

- (1) (2) The light source is a tungsten lamp and the incident light on the photocathode has a wavelength of 550 nm which is obtained through band pass filter.
- (2) (3) Overall control voltage: 0.8 V
- (3) Temp setting 25 °C

Date: April 16, 2009

Approved by: 

PRELIMINARY**H10770(P)A-40/-50 Specifications****PROTECTION CIRCUIT 50 μ A****Maximum Ratings**

Parameter	-40/-50 ^{*1}	Unit
Main unit input voltage	+18	V dc
Operating temperature	+5 to +25	Cel
Storage temperature	-20 to +50	Cel
Output Current	2	μ A
Control Voltage (Vcontrol)	+0.9(Input impedance for Vcont. is 100 k Ω)	V

*1 with protection circuit / limit 50 μ A**Specifications General**

(Ta = 25 Cel)

Parameter	-40	-50	Unit
Spectral response	300 to 720	380 to 890	nm
High voltage power supply and Voltage Regulator Supply voltage range	+11.5 to +15.5		V dc
High voltage power supply and Voltage Regulator Supply Current Requirement (Maximum)	62		mA
Supply Adjustable Range (Relative Sensitivity)	1:50		-
Setting Time(Sensitivity Control) ^{*1}	0.2		s
Effective Area (dia.)	5		mm
Weight (Approx.)	110		g

*1) Stabilized time in the control voltage adjustment from +1.0 V to +0.5 V.

Series Characteristics

(Ta = 25 Cel)

Parameter		-40	-50	Unit
H10770A	Radiant Sensitivity	at 420 nm	54	Typical $\times 10^{-6}$ A/nW
		at 550 nm	88	
		at 800 nm	-	
Dark Current ^{(A) (B)}	Typical	3.3	4.1	nA
	Maximum	9.3	11.6	
H10770PA	Radiant Sensitivity	at 420 nm	108	Typical $\times 10^{-8}$ A/nW
		at 550 nm	176	
		at 800 nm	-	
Dark Count ^{(B) (C)}	Typical	6000	7500	1/s
	Maximum	18000	22500	
Induced Ripple in Signal ^(D)		0.6		Maximum mV p-p
Anode Pulse Rise Time ^(A)		1.00		ns
Recommended Control Voltage Range Vcontrol		+0.50 to +0.80		V

(A) Control Voltage : +0.8 V ; Temperature control at 25 Cel.

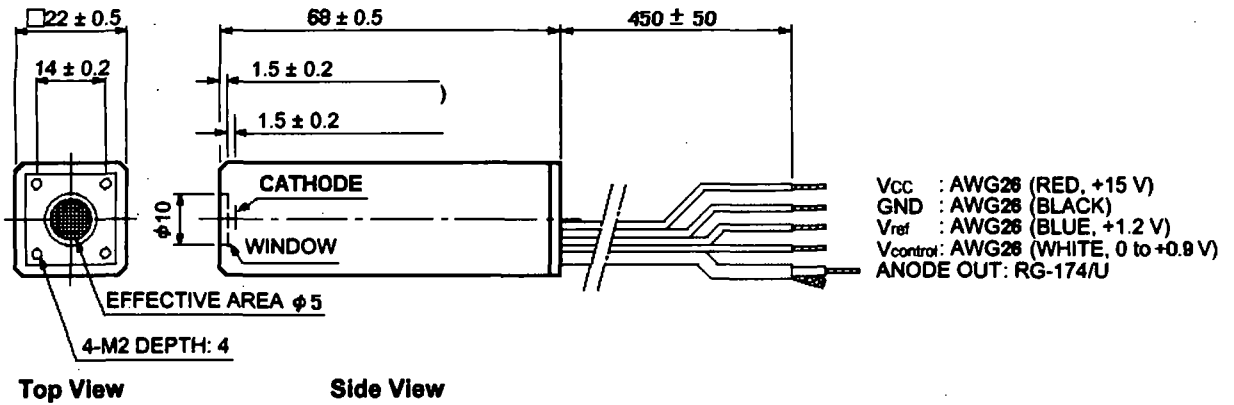
(B) After 30 min storage in darkness.

(C) Control Voltage : Plateau ; Temperature control at 25 Cel.

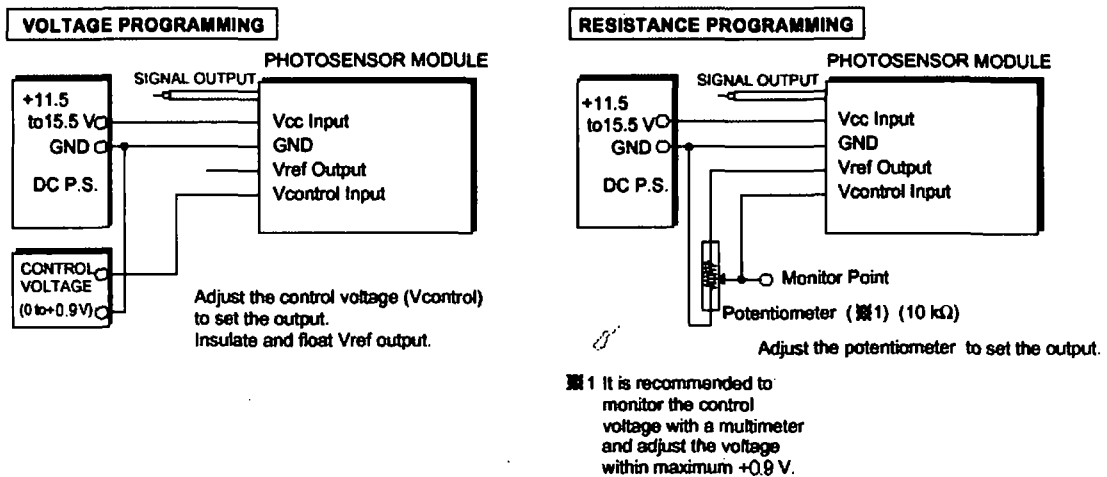
(D) Measured across 1 MOhm / 22 pF load

Dimensions

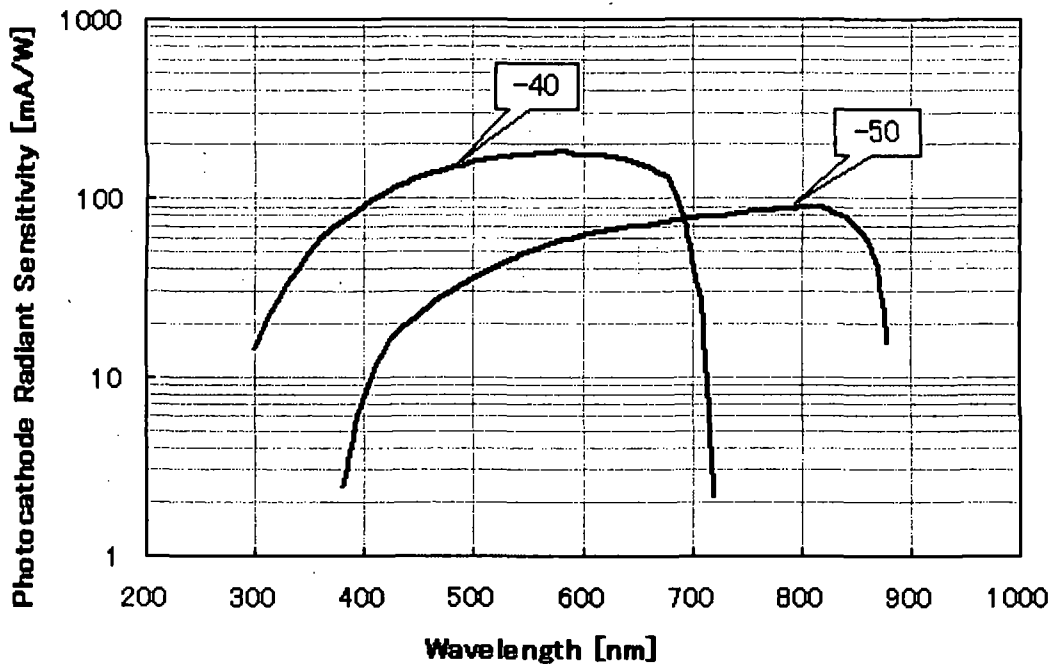
Unit : mm



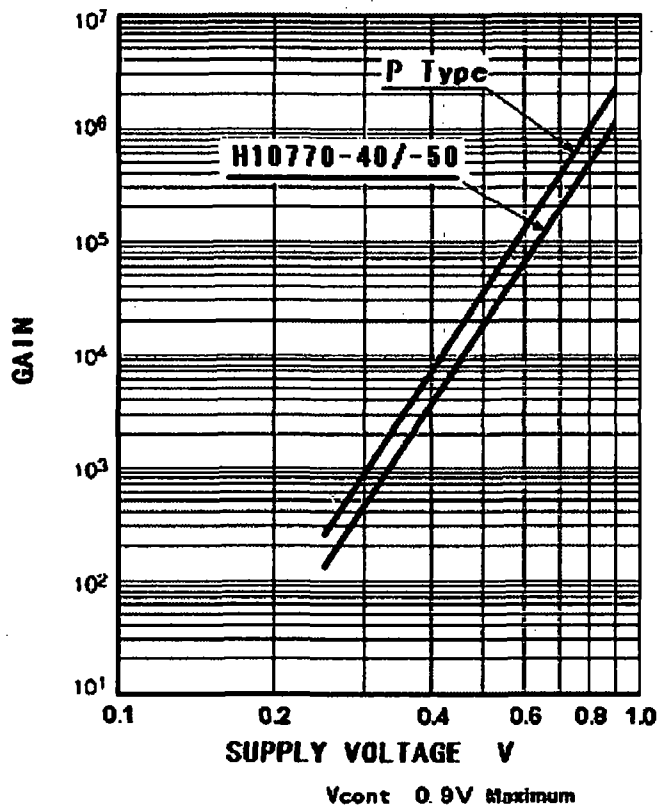
Wiring Examples For Sensitivity Adjustment



Typical Spectral Photocathode Radiant Sensitivity (H10770(P)A-40/-50)

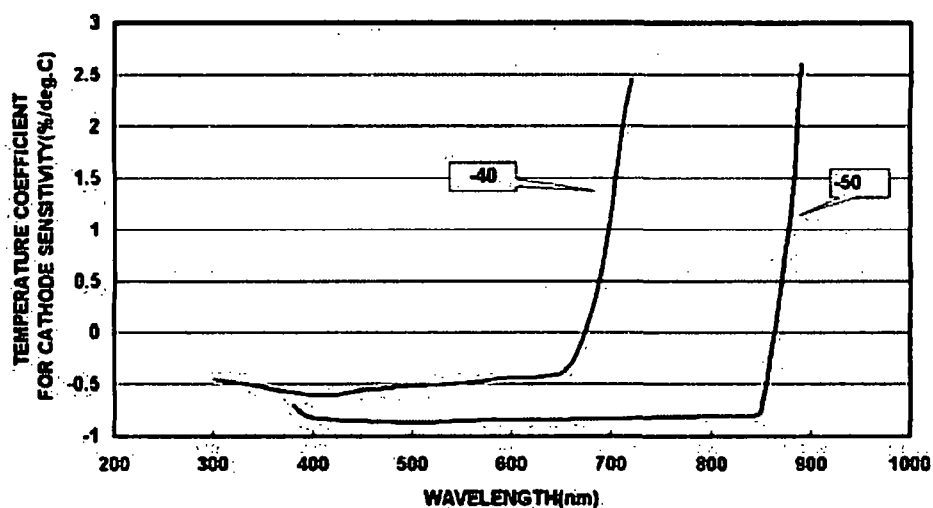


Typical Gain Characteristics (H10770(P)A-40/-50)



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Temperature Coefficient



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